

| Ref # | Hits   | Search Query                                | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|--------|---|---|------------------|---------|------------------|
| L1    | 115026 | BP or (boron near phosphide)                | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/11/27 16:29 |
| L2    | 205    | group-III near3 nitride near3 semiconductor | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/11/27 16:30 |
| L3    | 3705   | nitride near2 compound near2 semiconductor  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/11/27 16:30 |
| L4    | 27     | I1 and I2                                   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/11/27 16:30 |
| L5    | 22     | I1 and I3                                   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/11/27 16:31 |
| L6    | 26566  | GaN or (gallium near nitride)               | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/11/27 16:31 |
| L7    | 970    | I1 and I6                                   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/11/27 16:31 |
| L8    | 145    | I7 and amorphous                            | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/11/27 16:34 |